FAIRCHILD SEMICONDUCTOR®

February 2007

FDMS2572
N-Channel UltraFET Trench® MOSFET
150V, 27A, 47mΩ

Features

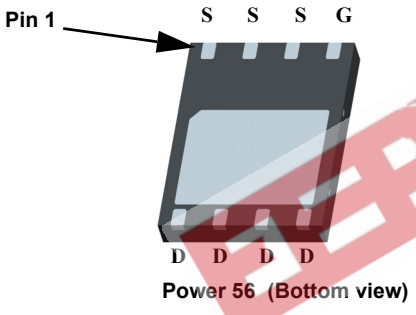
- Max $r_{DS(on)}$ = 47mΩ at V_{GS} = 10V, I_D = 4.5A
- Max $r_{DS(on)}$ = 53mΩ at V_{GS} = 6V, I_D = 4.5A
- Low Miller Charge
- Optimized efficiency at high frequencies
- UIS Capability (Single pulse and Repetitive pulse)
- RoHS Compliant

General Description

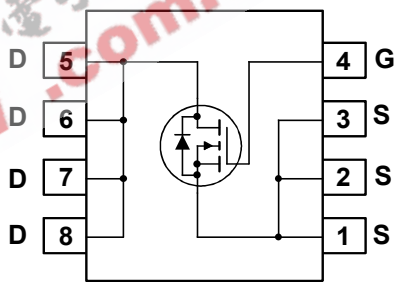
UltraFET devices combine characteristics that enable benchmark efficiency in power conversion applications. Optimized for $r_{DS(on)}$, low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

Application

- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier



Power 56 (Bottom view)



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			150	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous (Package limited)	T_C = 25°C		27	A
	-Continuous (Silicon limited)	T_C = 25°C		27	
	-Continuous	T_A = 25°C	(Note 1a)	4.5	
	-Pulsed			30	
P_D	Power Dissipation	T_C = 25°C		78	W
	Power Dissipation	T_A = 25°C	(Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

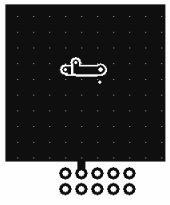
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS2572	FDMS2572	Power 56	13”	12mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted

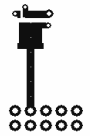
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		180		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120V, V_{GS} = 0V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2	3	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-9.8		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10V, I_D = 4.5A		36	47	mΩ
		V_{GS} = 6V, I_D = 4.5A		39	53	
		V_{GS} = 10V, I_D = 4.5A, T_J = 125°C		69	103	
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 4.5A		14		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 75V, V_{GS} = 0V, f = 1MHz		1960	2610	pF
C_{oss}	Output Capacitance			130	175	pF
C_{rss}	Reverse Transfer Capacitance			30	45	pF
R_g	Gate Resistance	f = 1MHz		1.3		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 75V, I_D = 1.0A, V_{GS} = 10V, R_{GEN} = 6Ω		11	20	ns
t_r	Rise Time			8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			38	61	ns
t_f	Fall Time			31	50	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{GS} = 0V to 10V, V_{DD} = 75V, I_D = 4.5A		31	43	nC
Q_{gs}	Gate to Source Gate Charge			9		nC
Q_{gd}	Gate to Drain “Miller” Charge			7		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 2.2A (Note 2)		0.7	1.0	V
t_{rr}	Reverse Recovery Time	I_F = 4.5A, di/dt = 100A/μs		67	101	ns
Q_{rr}	Reverse Recovery Charge			130	195	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a.50°C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 125°C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

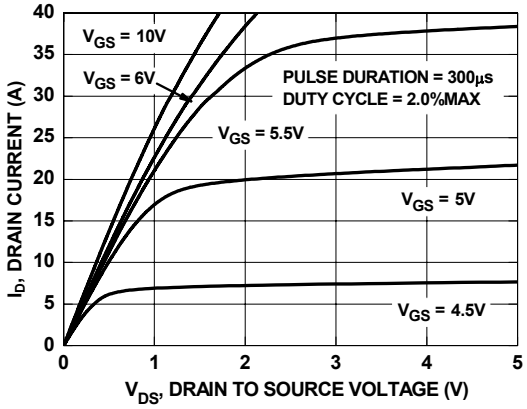


Figure 1. On-Region Characteristics

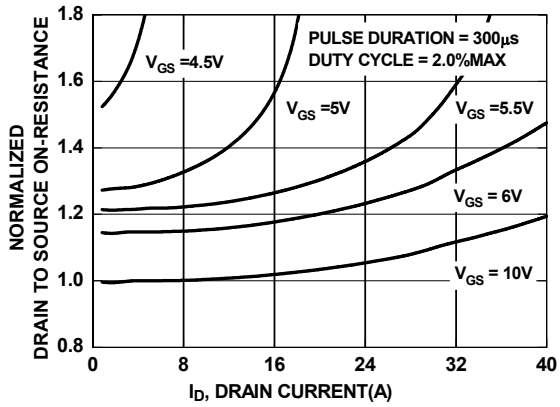


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

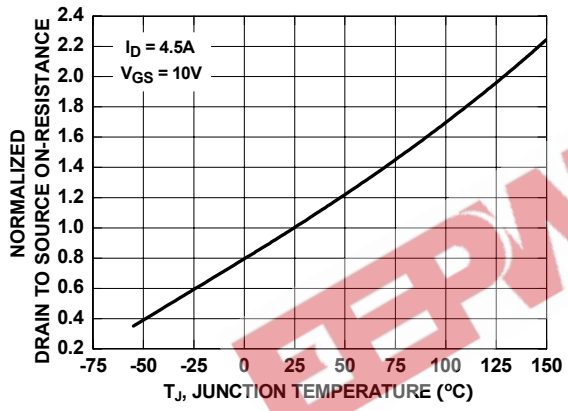


Figure 3. Normalized On-Resistance vs Junction Temperature

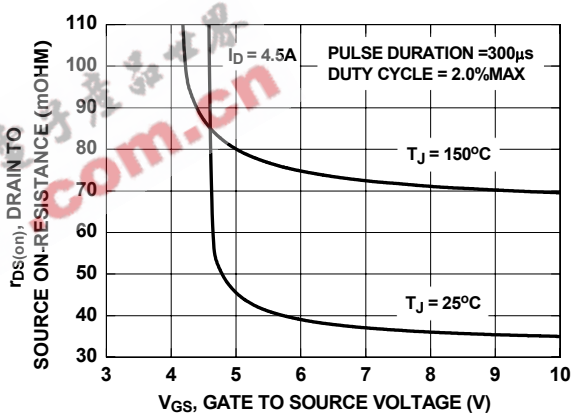


Figure 4. On-Resistance vs Gate to Source Voltage

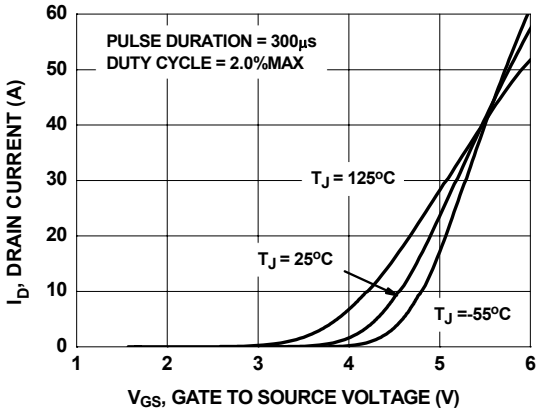


Figure 5. Transfer Characteristics

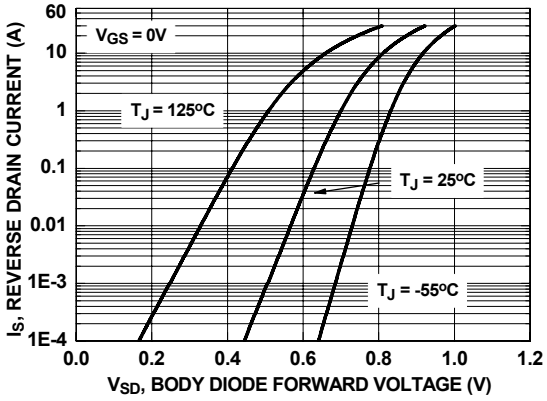


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

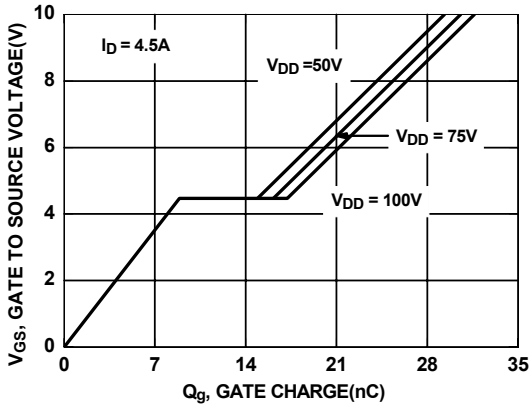


Figure 7. Gate Charge Characteristics

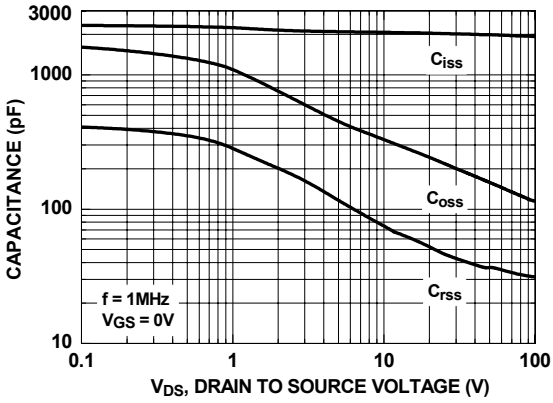


Figure 8. Capacitance vs Drain to Source Voltage

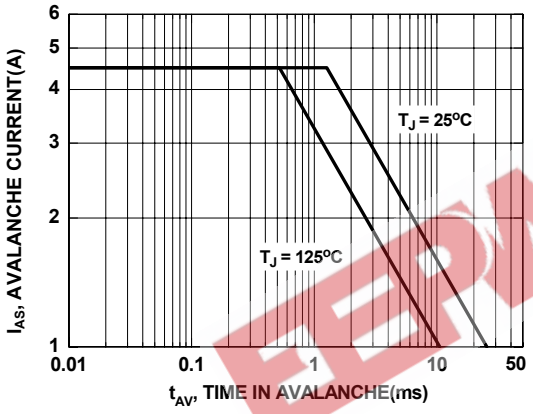


Figure 9. Unclamped Inductive Switching Capability

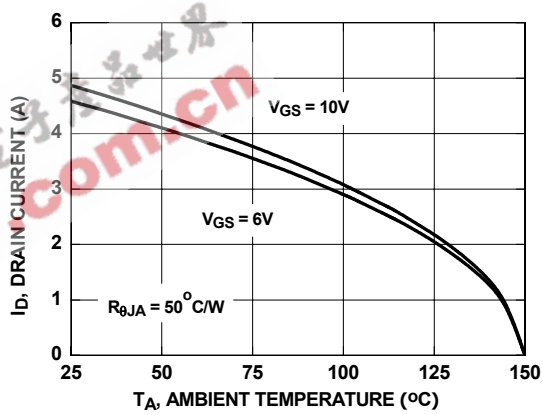


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

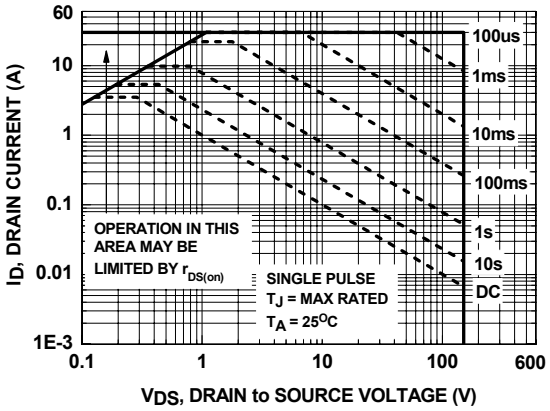


Figure 11. Forward Bias Safe Operating Area

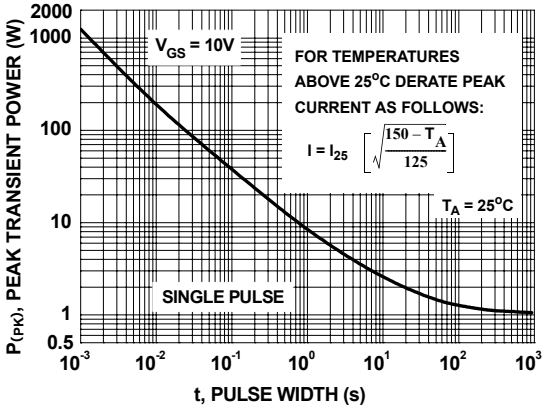


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

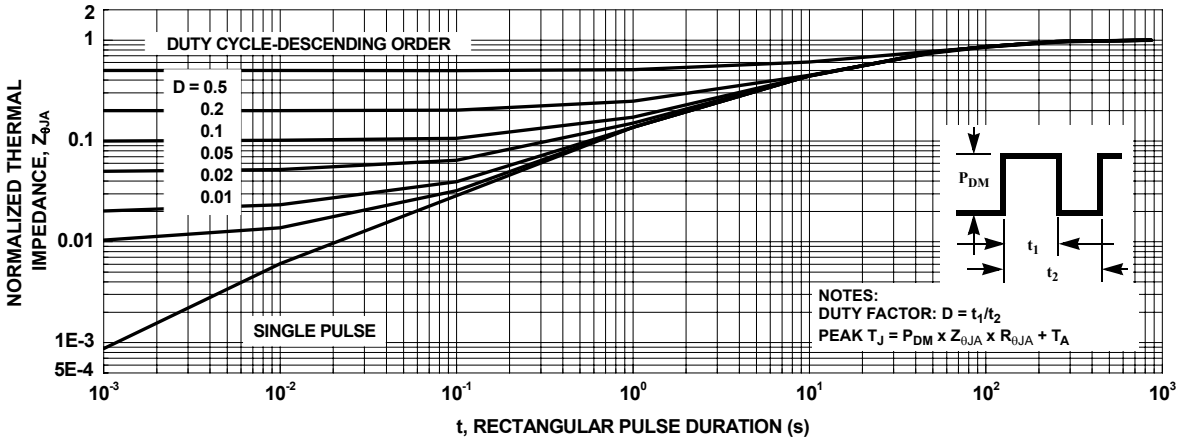
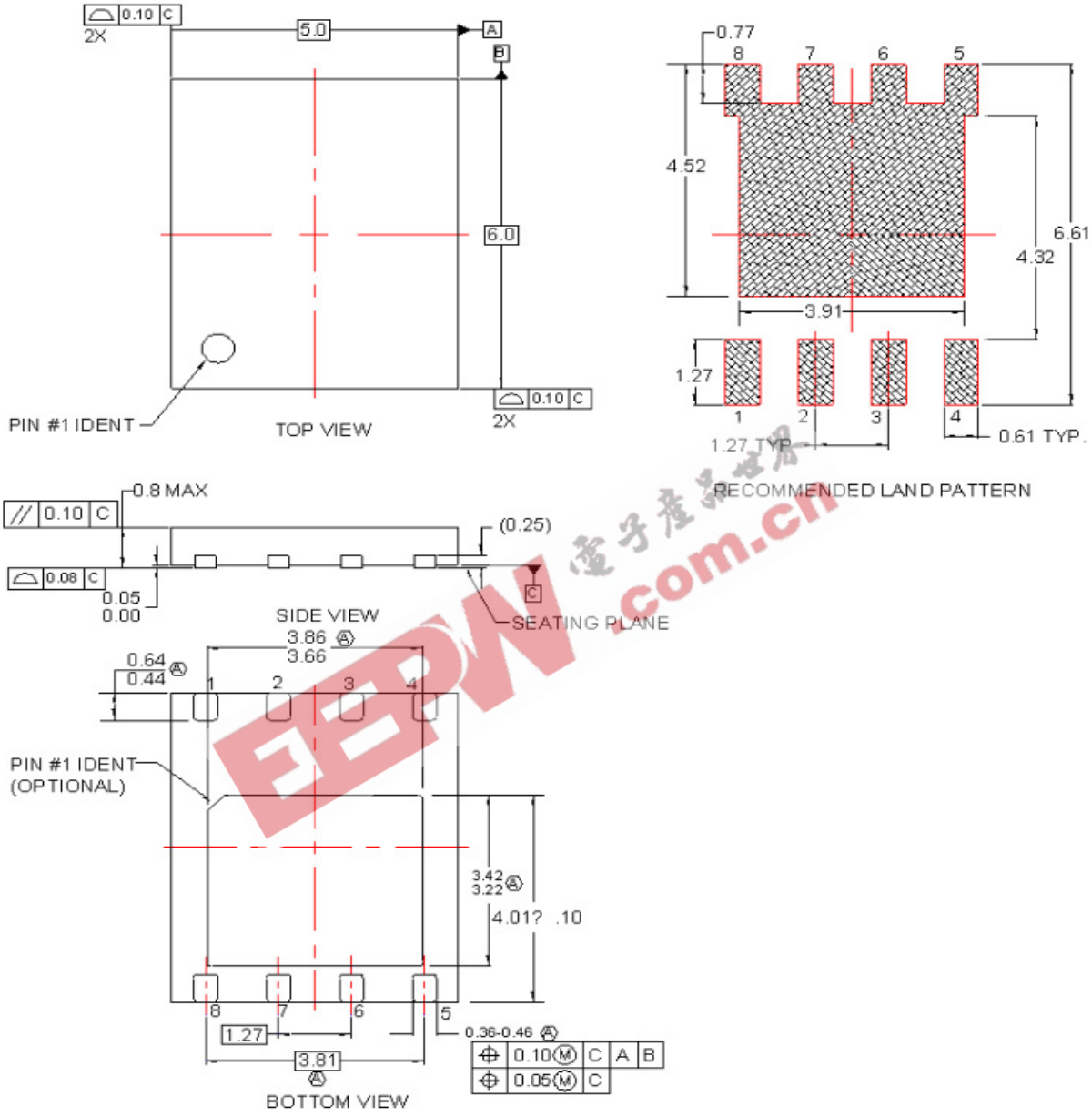


Figure 13. Transient Thermal Response Curve



NOTES:

A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229, DATED 11/2001.

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994

D. TERMINALS 5,6,7 AND 8 ARE TIED TO THE EXPOSED PADDLE

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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